Solid State Physics, Devices & Electronics – 20 MCQs with Detailed Solutions

JSSC CGL Technical (Physics) - Practice Set with Explanations

1) Bragg's law for X-ray diffraction from lattice planes is:

- (a) $n\lambda = 2d \cos\theta$
- (b) $n\lambda = 2d \sin\theta$
- (c) $n\lambda = d \sin\theta$
- (d) $n\lambda = d \cos\theta$

Correct Answer: (b)

Explanation: In a crystal, reflections from successive lattice planes separated by interplanar spacing d interfere constructively when the extra path 2d sin θ equals an integer multiple of the wavelength: $n\lambda = 2d \sin\theta$. This condition comes from setting phase difference = $2\pi n$.

2) Number of distinct Bravais lattices in 3D is:

- (a) 7
- (b) 14
- (c) 21
- (d) 32

Correct Answer: (b)

Explanation: There are 7 crystal systems (cubic, tetragonal, orthorhombic, hexagonal, rhombohedral, monoclinic, triclinic). Accounting for primitive/centered types gives 14 unique 3D Bravais lattices.

3) Which one is an amorphous solid?

- (a) NaCl
- (b) Glass
- (c) Diamond
- (d) Silicon

Correct Answer: (b)

Explanation: Amorphous solids lack long-range periodic order (random network), e.g., glass. NaCl, diamond, and crystalline silicon have long-range periodic lattices (crystalline).

4) A typical band gap of an insulator is:

- (a) < 1 eV
- (b) 1-3 eV
- (c) > 5 eV
- (d) 0 eV

Correct Answer: (c)

Explanation: Insulators have a large forbidden gap (Eg usually > 5 eV), semiconductors have small Eg (\sim 0.5–3 eV), and metals effectively have Eg \approx 0 due to overlapping bands.

5) In an n-type semiconductor, the majority carriers are:

- (a) Holes
- (b) Electrons
- (c) Electrons and holes equally
- (d) Protons

Correct Answer: (b)

Explanation: n-type doping (donors) adds extra electrons to the conduction band \rightarrow electrons are majority carriers, holes are minority.

6) Dulong-Petit law gives the molar heat capacity (Cv) of a crystalline solid (high T) as:

- (a) 3R
- (b) R
- (c) 2R
- (d) (3/2)R

Correct Answer: (a)

Explanation: Classically, each atom contributes 3 translational vibrational modes with energy kT per degree of freedom \rightarrow per mole Cv \approx 3R at high temperature (equipartition).

7) Low-temperature specific heat ($Cv \propto T^3$) is explained by:

- (a) Dulong-Petit Law
- (b) Einstein Model
- (c) Debye Model
- (d) Joule's Law

Correct Answer: (c)

Explanation: Debye treated lattice vibrations as acoustic phonons with a cutoff (Debye frequency). Density of states $\propto \omega^2$ leads to $Cv \propto T^3$ at low T, matching experiments.

8) Diamagnetic materials have magnetic susceptibility (χ):

- (a) Small positive
- (b) Small negative
- (c) Very large positive
- (d) Zero

Correct Answer: (b)

Explanation: Diamagnetism arises from Lenz-like induced currents opposing the applied field; χ is negative and very small in magnitude.

9) Expulsion of magnetic flux from a superconductor is called:

- (a) Faraday Effect
- (b) Meissner Effect
- (c) Hall Effect
- (d) Josephson Effect

Correct Answer: (b)

Explanation: Meissner effect: below Tc, a superconductor expels magnetic field ($B\rightarrow 0$ in bulk), showing it is a distinct thermodynamic phase, not merely a perfect conductor.

10) Current across a Josephson junction at zero voltage is carried by:

- (a) Electrons
- (b) Holes
- (c) Cooper pairs
- (d) Protons

Correct Answer: (c)

Explanation: Two superconductors separated by a thin barrier allow tunneling of paired electrons (Cooper pairs), giving a DC supercurrent $I = Ic \sin \phi$ at zero voltage; under DC voltage V, AC Josephson current with frequency 2eV/h appears.

11) A p-n junction diode is primarily used for:

- (a) Amplification
- (b) Rectification
- (c) Oscillation

(d) Modulation

Correct Answer: (b)

Explanation: Forward bias \rightarrow low resistance; reverse bias \rightarrow high resistance. This asymmetric I–V enables

AC→DC rectification.

12) A BJT used as an amplifier is biased to operate in the:

- (a) Cut-off region
- (b) Saturation region
- (c) Active region
- (d) Breakdown region

Correct Answer: (c)

Explanation: Active region (base-emitter forward biased, base-collector reverse biased) provides linear amplification of signals.

13) Which device is voltage-controlled?

- (a) BJT
- (b) FET/JFET
- (c) Transformer
- (d) Diode

Correct Answer: (b)

Explanation: In FETs, the channel conduction is controlled by gate-source voltage (VGS). BJTs are current-controlled (base current controls collector current).

jits2simple 14) The (amplitude) gain of an amplifier is:

- (a) Input/Output
- (b) Output/Input
- (c) Input × Output
- (d) Output Input

Correct Answer: (b)

Explanation: Voltage (or current) gain Av = Vout/Vin (or lout/lin). Power gain = Pout/Pin. In decibels: G(dB) = 20 log10 Av (voltage/current) or 10 log10 (power).

15) Which gate is a universal gate?

- (a) AND
- (b) OR
- (c) NAND
- (d) XOR

Correct Answer: (c)

Explanation: NAND (and similarly NOR) is functionally complete: any logic function can be implemented using only NAND gates.

16) De Morgan's law states: overline(A B) equals:

- (a) A**■** + B
- (b) A**■** · B
- (c) A + B
- (d) A · B

Correct Answer: (a)

Explanation: De Morgan's laws: overline(A ⋅ B) = A■ + B■ and overline(A + B) = A■ ⋅ B■. They follow from set/Boolean duality and truth tables.

17) XOR gate output is 1 when:

- (a) Inputs are both 0
- (b) Inputs are both 1
- (c) Inputs are different
- (d) Inputs are same

Correct Answer: (c)

Explanation: Exclusive-OR is 'odd parity': output 1 iff the number of 1's among inputs is odd; for two inputs, it's when inputs differ.

18) Which is NOT a secondary memory device?

- (a) Hard Disk
- (b) Pendrive
- (c) RAM
- (d) DVD

Correct Answer: (c)

Explanation: RAM is primary (volatile) memory; HDD, USB drives, and DVDs are non-volatile secondary storage.

19) The unit that performs arithmetic and logic operations in a microprocessor is:

- (a) Control Unit
- (b) ALU
- (c) Register
- (d) Memory

Correct Answer: (b)

Explanation: ALU (Arithmetic Logic Unit) executes operations like add, subtract, AND, OR, XOR, shifts. Control Unit sequences instructions; registers store operands; memory stores programs/data.

20) The room-temperature band gap of Silicon is closest to:

- (a) 0 eV
- (b) 1.1 eV
- (c) 3.5 eV
- (d) 5 eV

Correct Answer: (b)

Explanation: At 300 K, Silicon has Eg \approx 1.12 eV. Germanium \approx 0.66 eV; GaAs \approx 1.42 eV; insulators have Eg > 5 eV.

Tip: Mark any questions you missed and revisit the corresponding concept in your revision sheet.